PBSS5240X 40 V, 2 A PNP low VCEsat (BISS) transistor 19 October 2012

Product data sheet

1. Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 Surface-Mounted Device (SMD) plastic package. NPN complement: PBSS4240X.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency due to less heat generation

1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

1.4 Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-40	V
I _C	collector current			-	-	-2	А
I _{CM}	peak collector current			-	-	-3	А
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C		-	-	310	mΩ
I _{CRM}	repetitive peak collector current	$t_p \leq 20$ ms; $\delta \leq 0.33$; pulsed		-	-	-2.5	A

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		C L
2	С	collector		в
3	В	base		E
			SOT89	sym132

3. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PBSS5240X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89					

4. Marking

Table 4. Marking codes	Marking codes					
Type number	Marking code					
PBSS5240X	S48					

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-40	V
V _{CEO}	collector-emitter voltage	open base		-	-40	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-2	А
I _{CRM}	repetitive peak collector current	$\delta \leq 0.33$; $t_p \leq 20$ ms; pulsed		-	-2.5	А
I _{CM}	peak collector current			-	-3	А
I _B	base current			-	-300	mA
I _{BM}	peak base current			-	-1	А
P _{tot}	total power dissipation		[1]	-	0.5	W
			[2]	-	0.95	W

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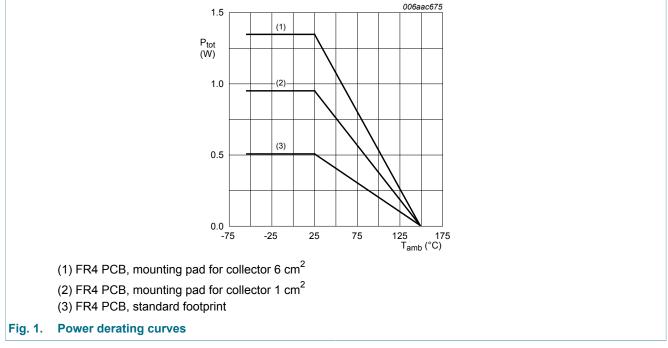
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Symbol	Parameter	Conditions		Min	Max	Unit
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



6. Thermal characteristics

Table 6. The	ermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	132	K/W
			[3]	-	-	93	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

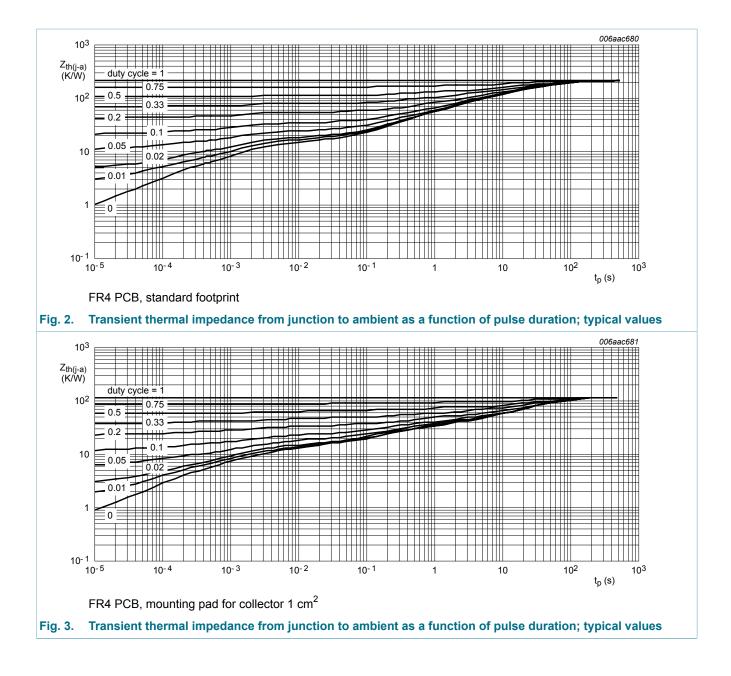
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



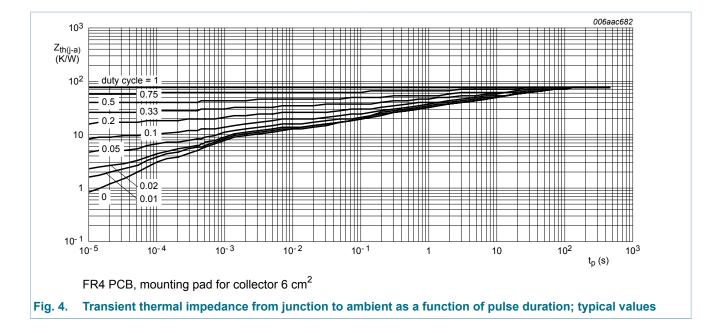
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7. Characteristics

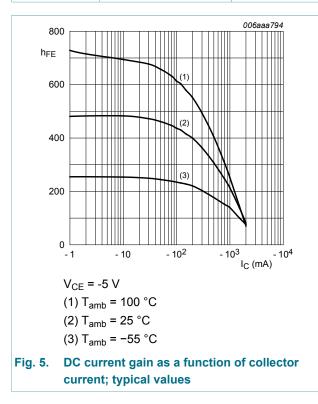
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V_{CB} = -40 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -40 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CEO}	collector-emitter cut-off current	V_{CE} = -30 V; I _B = 0 A; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO} emitter-base cut-off current		V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I _C = -1 mA; T _{amb} = 25 °C	300	-	-	
		V_{CE} = -5 V; I _C = -500 mA; T _{amb} = 25 °C	215	-	-	
		V _{CE} = -5 V; I _C = -1 A; T _{amb} = 25 °C	145	-	-	
		V_{CE} = -5 V; I _C = -2 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	55	-	-	
V _{CEsat}	collector-emitter	I_{C} = -100 mA; I_{B} = -5 mA; T_{amb} = 25 °C	-	-	-140	mV
	saturation voltage	I _C = -500 mA; I _B = -50 mA; T _{amb} = 25 °C	-	-	-170	mV
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	-310	mV
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	-630	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	310	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	-1.2	V
V _{BEon}	base-emitter turn-on voltage	$\begin{split} V_{CE} &= -5 \text{ V; } \text{I}_{C} = -1 \text{ A; pulsed;} \\ t_{p} &\leq 300 \text{\mu}\text{s; } \delta \leq 0.02 \text{ ; } \text{T}_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-	-1.1	V
f _T	transition frequency	V_{CE} = -10 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	150	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	12	pF



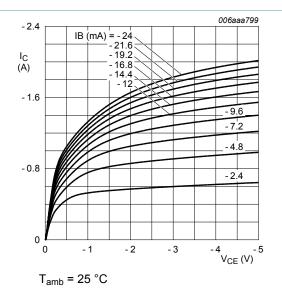
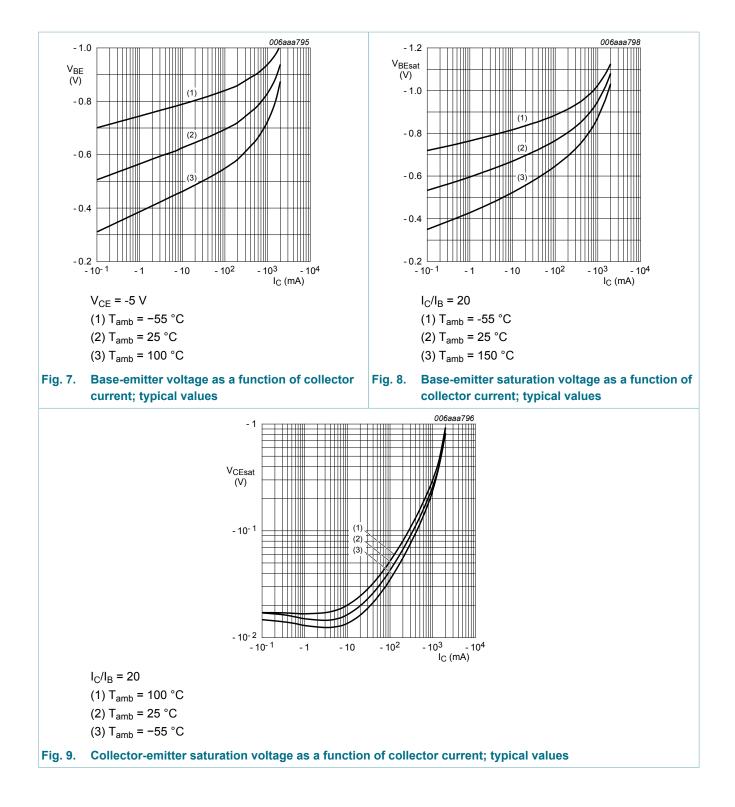


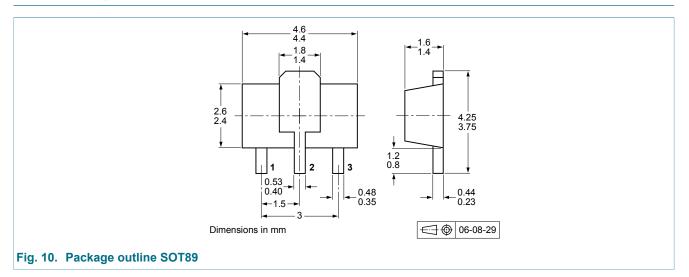
Fig. 6. Collector current as a function of collectoremitter voltage; typical values

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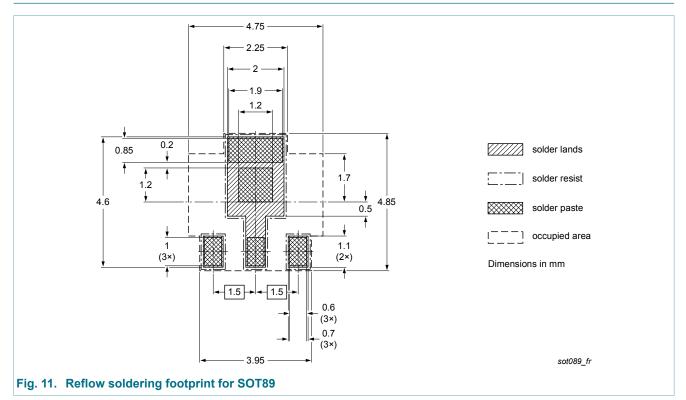


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8. Package outline



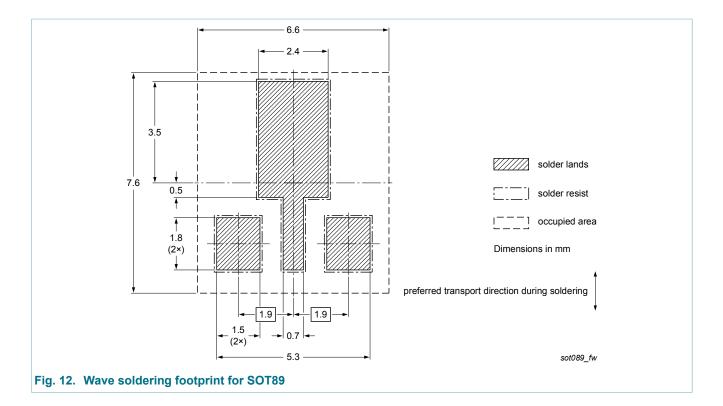
9. Soldering



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10. Revision history

Table	8.	Revision his	story	
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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5240X v.1	20121019	Product data sheet	-	-

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11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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